

Title (en)
SILICON CARBIDE POWDER, METHOD FOR MANUFACTURING THE SAME AND METHOD FOR MANUFACTURING SILICON CARBIDE
INGOT USING THE SAME

Title (de)
SILICIUMCARBIDPULVER, VERFAHREN ZUR HERSTELLUNG DAVON UND VERFAHREN ZUR HERSTELLUNG EINES
SILICIUMCARBIDBLOCKS DAMIT

Title (fr)
POUDRE DE CARBURE DE SILICIUM, SON PROCÉDÉ DE FABRICATION ET PROCÉDÉ DE FABRICATION DE LINGOT DE CARBURE DE
SILICIUM L'UTILISANT

Publication
EP 4328181 A1 20240228 (EN)

Application
EP 23192080 A 20230818

Priority
KR 20220104820 A 20220822

Abstract (en)
A silicon carbide powder including carbon; silicon; and an oxide film having a thickness of 0.1 nm to 10 nm.

IPC 8 full level
C01B 32/956 (2017.01); **C01B 32/963** (2017.01); **C01B 32/984** (2017.01)

CPC (source: EP US)
C01B 32/956 (2017.08 - EP); **C30B 23/02** (2013.01 - US); **C30B 23/025** (2013.01 - EP); **C30B 29/36** (2013.01 - EP US);
C30B 35/007 (2013.01 - EP US); **C01P 2002/90** (2013.01 - EP); **C01P 2004/60** (2013.01 - EP)

Citation (applicant)
JP 2002326876 A 20021112 - BRIDGESTONE CORP

Citation (search report)

- [A] US 10822720 B1 20201103 - PARK JONG HWI [KR], et al
- [A] KR 20130000509 A 20130103 - LG INNOTEK CO LTD [KR]
- [A] US 2021123160 A1 20210429 - PARK JONG HWI [KR], et al
- [A] US 2021123843 A1 20210429 - PARK JONG HWI [KR], et al

Designated contracting state (EPC)
AL AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC ME MK MT NL NO PL PT RO RS SE SI SK SM TR

Designated extension state (EPC)
BA

Designated validation state (EPC)
KH MA MD TN

DOCDB simple family (publication)
EP 4328181 A1 20240228; JP 2024029763 A 20240306; KR 102567936 B1 20230817; TW 202408927 A 20240301;
US 2024060212 A1 20240222

DOCDB simple family (application)
EP 23192080 A 20230818; JP 2023133151 A 20230817; KR 20220104820 A 20220822; TW 112130863 A 20230817;
US 202318448165 A 20230811